

ABSTRACT OF THE DISCLOSURE

A method for creating electrical pathways for semiconductor device structures using laser machining processes is provided. The method of the present invention includes providing a semiconductor substrate and forming one or more depressions in the semiconductor substrate using laser machining processes. Optionally, a film may be deposited over the semiconductor substrate and the depressions may be formed therein. Subsequently, the semiconductor substrate and/or film are etched to smooth out the depressions and the depressions are then filled with an electrically conductive material. The electrically conductive material is then planarized down to the surface of the semiconductor substrate or film thereby isolating the electrically conductive material in the depressions.

N:\2269\5665\2nd.Rev.draft.app.doc